

• General Description

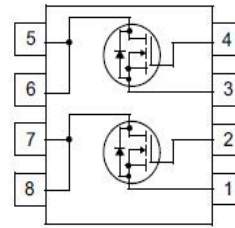
The ZMD68203S combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

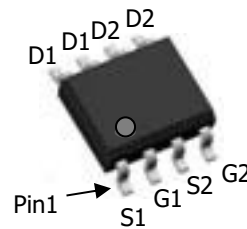
- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Dual DIE in one package

• Application

- Power Management in Notebook Computer,
- Portable Equipment and Battery Powered Systems

• Product Summary


$V_{DS1} = 20V$
 $V_{DS2} = 20V$
 $R_{DS(ON)1} = 22m\Omega$
 $R_{DS(ON)2} = 22m\Omega$
 $I_{D1} = 5.0A$
 $I_{D2} = 5.0A$



SOP8

• Ordering Information:

Part NO.	ZMD68203S
Marking	ZMD68203
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	5.0	A
	$I_{D@TC=75^\circ C}$	3.8	A
	$I_{D@TC=100^\circ C}$	3.2	A
Pulsed Drain Current ^①	I_{DM}	13	A
Total Power Dissipation	$P_D@TC=25^\circ C$	3.6	W
Total Power Dissipation	$P_D@TA=25^\circ C$	0.69	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	10	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	34	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	180	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	0.3	0.75	1.2	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 6.5A$		22	26.5	$m\Omega$
		$V_{GS} = 2.5V, I_D = 5A$		26	33	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 5A$		3		S
Source-drain voltage	V_{SD}	$I_S = 5.0A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	470	-	pF
Output capacitance	C_{oss}		-	115	-	
Reverse transfer capacitance	C_{rss}		-	50	-	

•Gate Charge characteristics($T_a = 25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$	-	6	-	nC
Gate - Source charge	Q_{gs}	$I_D = 5A$	-	2	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	3	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Gate-Charge Characteristics

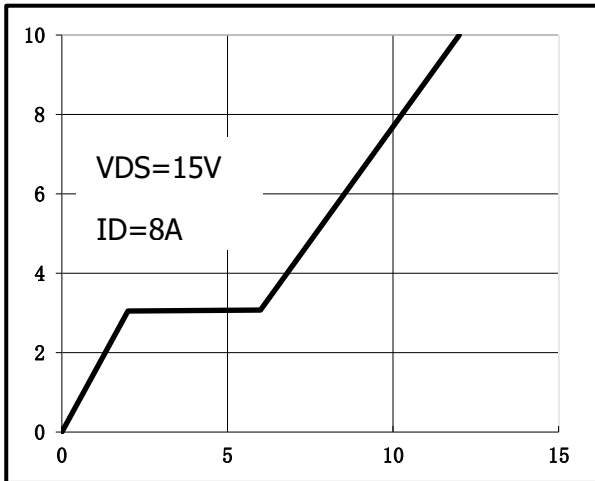


Fig.2 Capacitance Characteristics

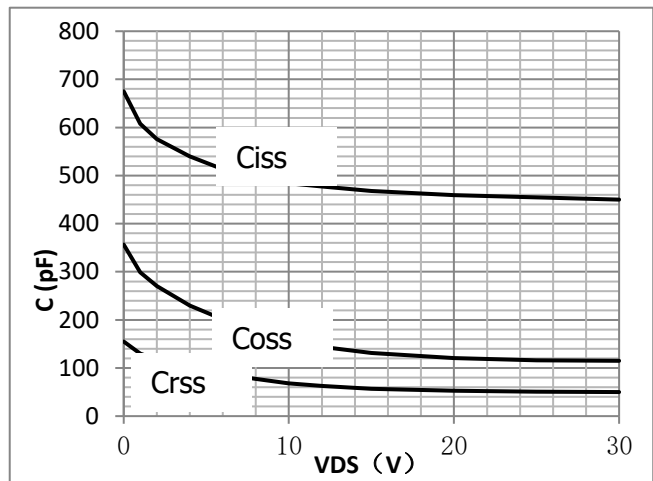


Fig.3 Power Dissipation Derating Curve

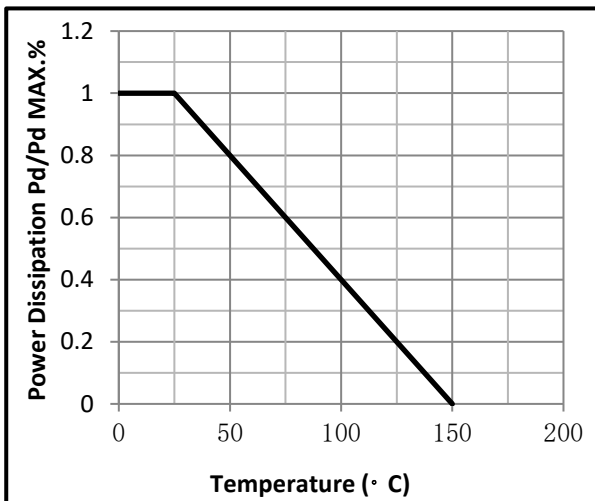


Fig.4 Typical output Characteristics

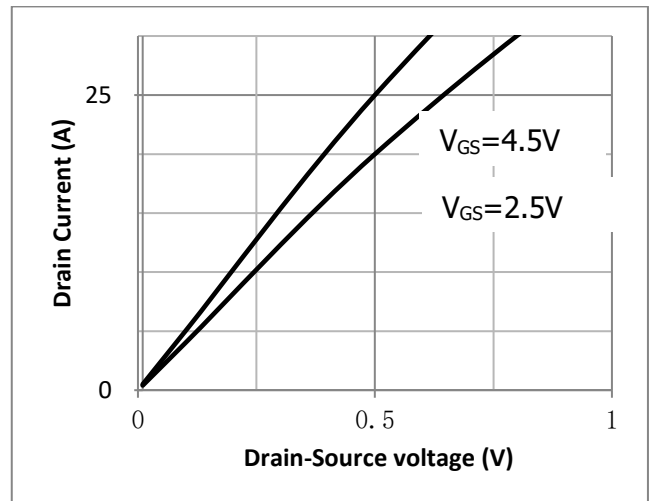


Fig.5 Threshold Voltage V.S Junction Temperature

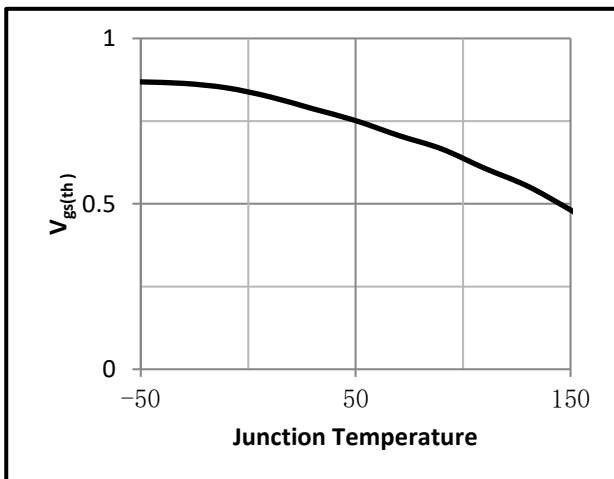


Fig.6 Resistance V.S Drain Current

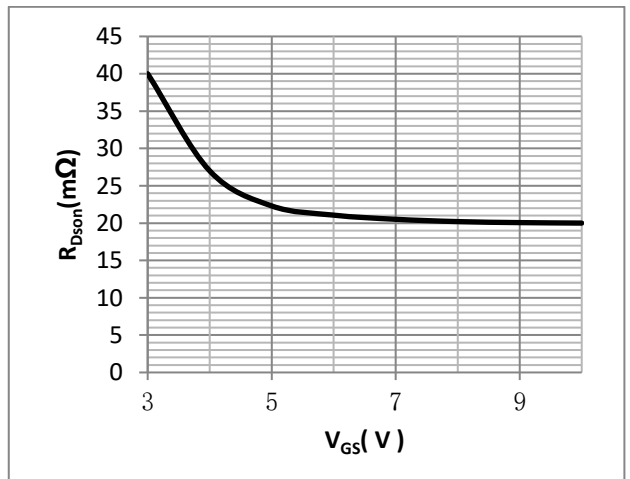


Fig.7 On-Resistance VS Gate Source Voltage

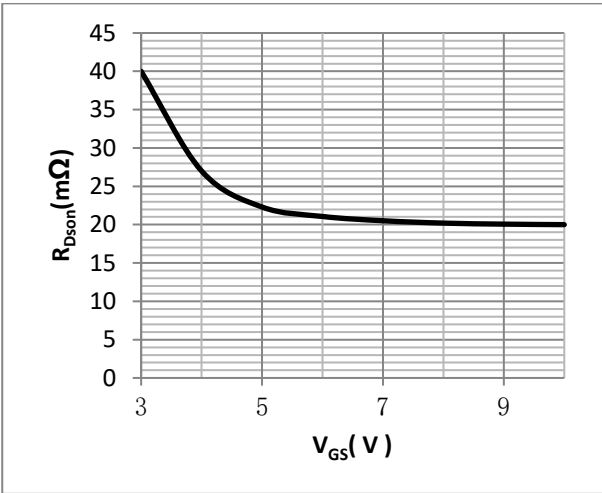


Fig.8 On-Resistance V.S Junction Temperature

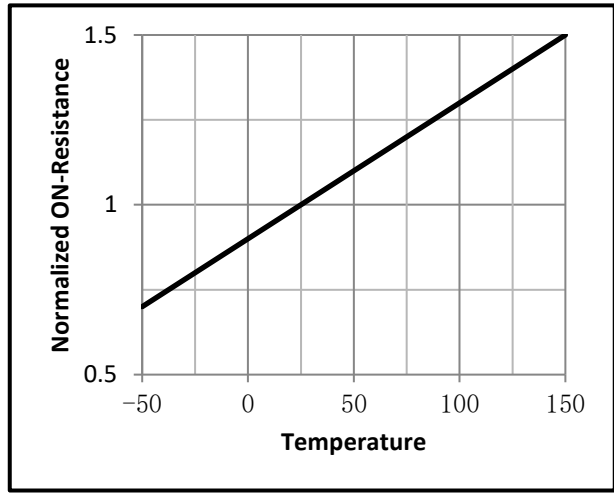


Fig.7 Switching Time Measurement Circuit

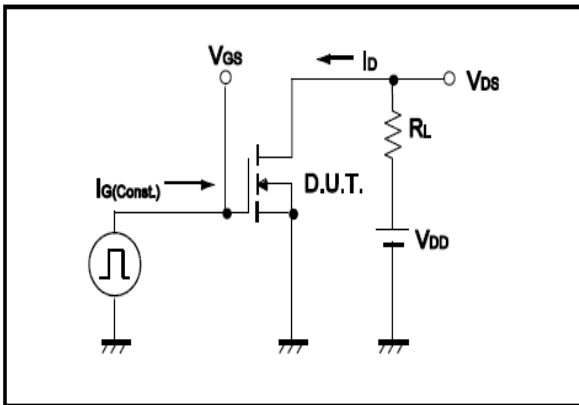


Fig.8 Gate Charge Waveform

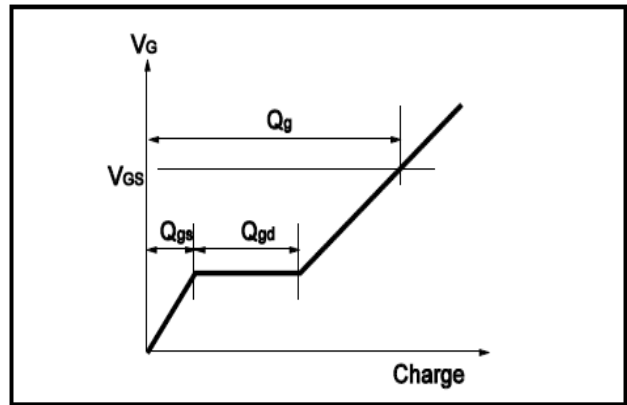


Fig.9 Switching Time Measurement Circuit

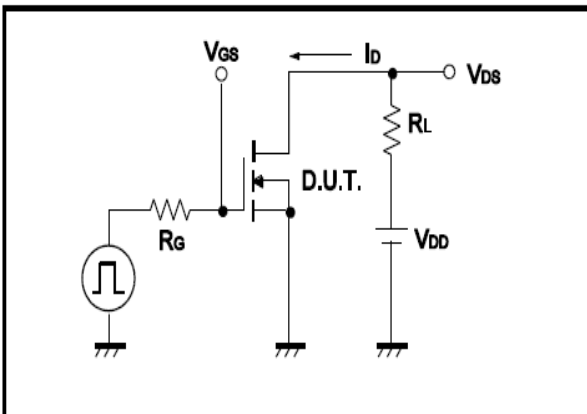


Fig.10 Gate Charge Waveform

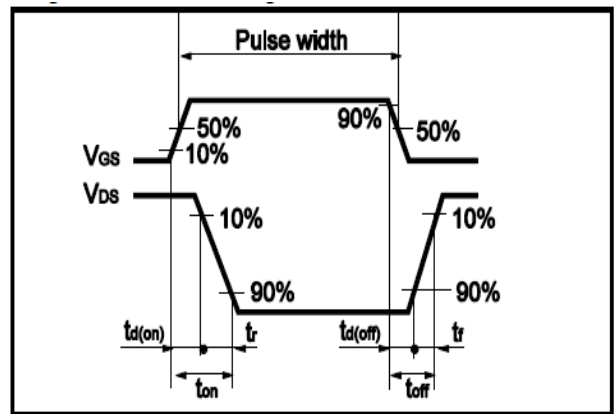


Fig.11 Avalanche Measurement Circuit

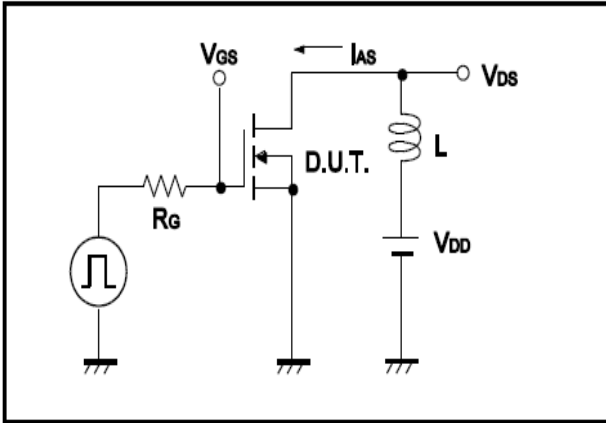
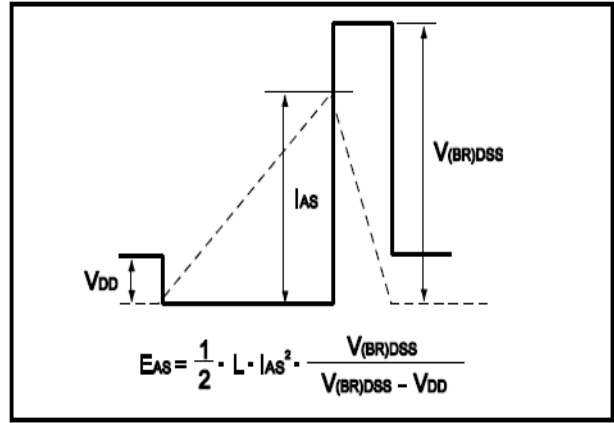


Fig.12 Avalanche Waveform



●Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.10	D		1.05	
B2		5.00		D1	0.40		0.62

